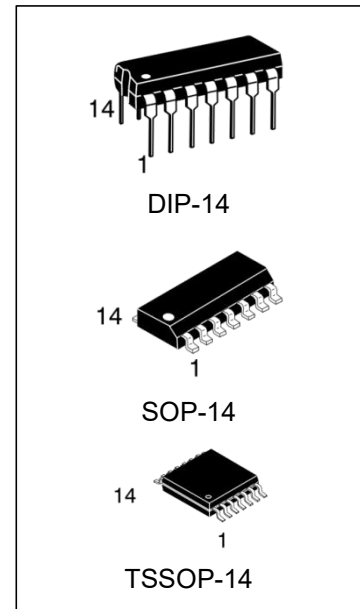


## CD4066 Quad Bilateral Switches

### Features:

- Wide supply voltage range from 3V to 9V
- Fully static operation
- 5V and 9V parametric ratings
- Standardized symmetrical output characteristics
- Inputs and outputs are protected against electrostatic effects
- Specified from -40°C to +85°C
- Packaging information: DIP14/SOP14/TSSOP14



### Ordering Information

DEVICE	Package Type	MARKING	Packing	Packing Qty
CD4066BE/ CD4066BN	DIP-14	CD4066B	TUBE	1000pcs/box
CD4066BM/TR	SOP-14	CD4066B	REEL	2500pcs/reel
CD4066BMT/TR	TSSOP-14	CD4066B	REEL	2500pcs/reel

## General Description

The CD4066B provides four single-pole, single-throw analog switch functions. Each switch has two input/output terminals (nY and nZ) and an active HIGH enable input (nE). When nE is LOW, the analog switch is turned off.

## Block Diagram

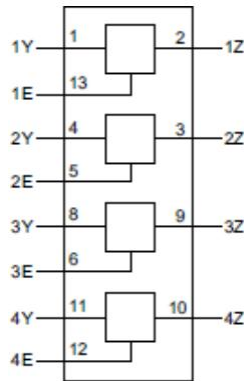


Figure 1. Functional diagram

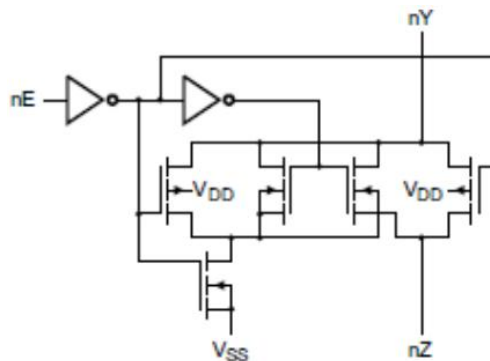


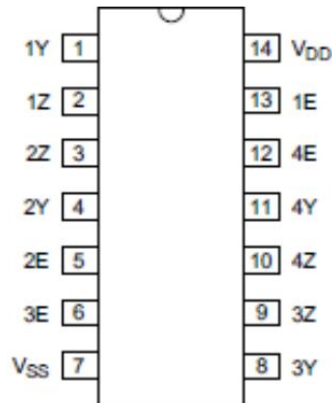
Figure 2. Logic diagram (one switch)

## Function Table

Input	Switch
nE	
H	ON
L	OFF

**Note:** H=HIGH voltage level; L=LOW voltage level.

## Pin Configurations



DIP-14/SOP-14/TSSOP-14

## Pin Description

Pin No.	Pin Name	Description
1	1Y	independent input or output
2	1Z	independent input or output
3	2Z	independent input or output
4	2Y	independent input or output
5	2E	enable input (active HIGH)
6	3E	enable input (active HIGH)
7	V <sub>SS</sub>	ground (0V)
8	3Y	independent input or output
9	3Z	independent input or output
10	4Z	independent input or output
11	4Y	independent input or output
12	4E	enable input (active HIGH)
13	1E	enable input (active HIGH)
14	V <sub>DD</sub>	supply voltage

## Absolute Maximum Ratings

(Voltages are referenced to  $V_{SS}$  (ground=0V), unless otherwise specified.)

Parameter	Symbol	Conditions	Min.	Max.	Unit
supply voltage	$V_{DD}$	-	-0.5	+12	V
input voltage	$V_I$	-	-0.5	$V_{DD}+0.5$	V
input clamping current	$I_{IK}$	$V_I < 0.5V$ or $V_I > V_{DD}+0.5V$	-	$\pm 10$	mA
input/output current	$I_{I/O}$	-	-	$\pm 10$	mA
storage temperature	$T_{stg}$	-	-65	+150	°C
total power dissipation	$P_{tot}$	-	-	500	mW
device dissipation	P	per output transistor	-	100	mW
Soldering temperature	$T_L$	10s	DIP	245	°C
			SOP		°C

- Note:**
- 1、 Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but specific performance is not ensured.
  - 2、 For DIP14 packages: above 70°C the value of  $P_{tot}$  derates linearly with 12mW/K.
  - 3、 For SOP14 packages: above 70°C the value of  $P_{tot}$  derates linearly with 8mW/K.
  - 4、 For (T)SSOP14 packages: above 60°C the value of  $P_{tot}$  derates linearly with 5.5mW/K.

## Recommended Operating Conditions

( $T_{amb}=25^\circ\text{C}$ ;  $R_L=10\text{k}\Omega$ ;  $C_L=50\text{pF}$ ;  $nE=V_{DD}$ ;  $V_{is}=V_{DD}=5V$ .)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
supply voltage	$V_{DD}$	-	3	5	9	V
ambient temperature	$T_{amb}$	in free air	-40	-	+85	°C
input voltage	$V_I$	-	0	-	$V_{DD}$	V
Disable output time (High level→turn off)	$t_{PHZ}$	nE to nZ or nE to nY	-	80	160	ns
Disable output time (Low level→turn off)	$t_{PLZ}$	nE to nZ or nE to nY	-	80	160	ns
Enable output time (turn off→high/low level)	$t_{PZH}, t_{PZL}$	-	-	45	90	ns
input capacitance	$C_I$	-	-	-	7.5	pF

## Electrical Characteristics

### DC Characteristics 1

( $T_{amb}=25^{\circ}\text{C}$ , voltages are referenced to  $V_{SS}$  (ground=0V), unless otherwise specified.)

Parameter	Symbol	Conditions (V)		$T_{amb}=25^{\circ}\text{C}$			Unit
				Min.	Typ.	Max.	
supply current	$I_{DD}$	$V_I=V_{DD}$ or $V_{SS}$ , $I_O=0\text{A}$	$V_{DD}=5\text{V}$	-	-	1.0	$\mu\text{A}$
			$V_{DD}=9\text{V}$	-	-	2.0	$\mu\text{A}$
HIGH-level input voltage	$V_{IH}$	$ I_O <1\mu\text{A}$	$V_{DD}=5\text{V}$ , $V_O=0.5\text{V}$ or $4.5\text{V}$	3.5	-	-	V
			$V_{DD}=9\text{V}$ , $V_O=0.5\text{V}$ or $8\text{V}$	7.0	-	-	V
LOW-level input voltage	$V_{IL}$	$ I_O <1\mu\text{A}$	$V_{DD}=5\text{V}$ , $V_O=0.5\text{V}$ or $4.5\text{V}$	-	-	1.5	V
			$V_{DD}=9\text{V}$ , $V_O=0.5\text{V}$ or $8\text{V}$	-	-	3.0	V
input leakage current	$I_i$	$V_I=0\text{V}$ or $9\text{V}$ , $V_{DD}=9\text{V}$		-	-	0.3	$\mu\text{A}$
ON resistance (rail)	$R_{ON}$	$V_I=0\text{V}$ to $V_{DD}-V_{EE}$	$V_{DD}-V_{EE}=5\text{V}$	-	350	2500	$\Omega$
			$V_{DD}-V_{EE}=9\text{V}$	-	80	245	$\Omega$
		$V_I=0\text{V}$	$V_{DD}-V_{EE}=5\text{V}$	-	115	340	$\Omega$
			$V_{DD}-V_{EE}=9\text{V}$	-	50	160	$\Omega$
		$V_I=V_{DD}-V_{EE}$	$V_{DD}-V_{EE}=5\text{V}$	-	120	365	$\Omega$
			$V_{DD}-V_{EE}=9\text{V}$	-	65	200	$\Omega$
ON resistance mismatch between channels	$\Delta R_{ON}$	$V_I=0\text{V}$ to $V_{DD}-V_{EE}$	$V_{DD}-V_{EE}=5\text{V}$	-	25	-	$\Omega$
			$V_{DD}-V_{EE}=9\text{V}$	-	10	-	$\Omega$

**Note:** On resistance waveform and test circuit see Figure 9 and Figure 10.

## DC Characteristics 2

( $T_{amb}=-40^{\circ}\text{C}$  to  $+85^{\circ}\text{C}$ , voltages are referenced to  $V_{SS}$  (ground=0V), unless otherwise specified.)

Parameter	Symbol	Conditions (V)	$T_{amb}=-40^{\circ}\text{C}$		$T_{amb}=+85^{\circ}\text{C}$		Unit	
			Min.	Max.	Min.	Max.		
supply current	$I_{DD}$	$V_i=V_{DD}$ or $V_{SS}$ , $I_o=0A$	$V_{DD}=5V$	-	1.0	-	7.5	$\mu A$
			$V_{DD}=9V$	-	2.0	-	15.0	$\mu A$
HIGH-level input voltage	$V_{IH}$	$ I_o <1\mu A$	$V_{DD}=5V$ , $V_o=0.5V$ or $4.5V$	3.5	-	3.5	-	V
			$V_{DD}=9V$ , $V_o=0.5V$ or $8V$	7.0	-	7.0	-	V
LOW-level input voltage	$V_{IL}$	$ I_o <1\mu A$	$V_{DD}=5V$ , $V_o=0.5V$ or $4.5V$	-	1.5	-	1.5	V
			$V_{DD}=9V$ , $V_o=0.5V$ or $8V$	-	3.0	-	3.0	V
input leakage current	$I_i$	$V_i=0V$ or $9V$ , $V_{DD}=9V$	-	-	-	1.0	$\mu A$	

## AC Characteristics 1

( $T_{amb}=25^{\circ}\text{C}$ ,  $V_{EE}=V_{SS}=0V$ ,  $t_r, t_f \leq 20ns$ ,  $C_L=50pF$ ,  $R_L=10k\Omega$ , unless otherwise specified.)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit	
HIGH to LOW propagation delay time	$t_{PHL}$	nY to nZ; nZ to nY; see Figure 4	$V_{DD}=5V$	-	10	20	ns
			$V_{DD}=9V$	-	5	10	ns
LOW to HIGH propagation delay	$t_{PLH}$	nY to nZ; nZ to nY; see Figure 4	$V_{DD}=5V$	-	10	20	ns
			$V_{DD}=9V$	-	5	10	ns
HIGH to OFF-state propagation delay	$t_{PHZ}$	nE to nY, nZ; see Figure 5	$V_{DD}=5V$	-	80	160	ns
			$V_{DD}=9V$	-	65	130	ns
LOW to OFF-state propagation delay	$t_{PLZ}$	nE to nY, nZ; see Figure 5	$V_{DD}=5V$	-	80	160	ns
			$V_{DD}=9V$	-	70	140	ns
OFF-state to HIGH propagation delay	$t_{PZH}$	nE to nY, nZ; see Figure 5	$V_{DD}=5V$	-	40	80	ns
			$V_{DD}=9V$	-	20	40	ns
OFF-state to LOW propagation delay	$t_{PZL}$	nE to nY, nZ; see Figure 5	$V_{DD}=5V$	-	45	90	ns
			$V_{DD}=9V$	-	20	40	ns

## AC Characteristics 2

( $T_{amb}=25^{\circ}C$ ,  $V_{EE}=V_{SS}=0V$ ,  $V_i=0.5V_{DD}$  (p-p), unless otherwise specified.)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit	
Square wave distortion	$d_{sin}$	see Figure 6; $R_L=10k\Omega$ ; $C_L=15pF$ ; channel ON; $f_i=1kHz$	$V_{DD}=5V$	0.25	-	-	%
			$V_{DD}=9V$	0.04	-	-	%
any two channel crosstalk	$f_{ct}$	$V_{DD}=9V$ , see note2	1	-	-	MHz	
crosstalk voltage (nE to nY to nZ)	$V_{ct}$	see Figure 7; $R_L=10k\Omega$ ; $C_L=15pF$ ; $\bar{E}$ or Sn= $V_{DD}$ (square-wave)	50	-	-	mV	
OFF frequency	$f_{OFF}$	$V_{DD}=9V$ , see note3	1	-	-	MHz	
conduction frequency	$f_{ON}$	$V_{DD}=5V$ , see note4	-	-	-	MHz	
		$V_{DD}=9V$ , see note4	90	-	-	MHz	

**Note:**

- (1)  $f_i$  is biased at  $0.5V_{DD}$ ;  $V_i=0.5V_{DD}$  (p-p).
- (2)  $R_L=1k\Omega$ ;  $20\log V_{os}/V_{is}=-50dB$ , see Figure 8.
- (3)  $R_L=1k\Omega$ ;  $C_L=5pF$ , channel off,  $20\log V_{os}/V_{is}=-50dB$ , see Figure 6.
- (4)  $R_L=1k\Omega$ ;  $C_L=5pF$ , channel on,  $20\log V_{os}/V_{is}=-3dB$ , see Figure 6.

## Testing Circuit

### AC Testing Circuit 1

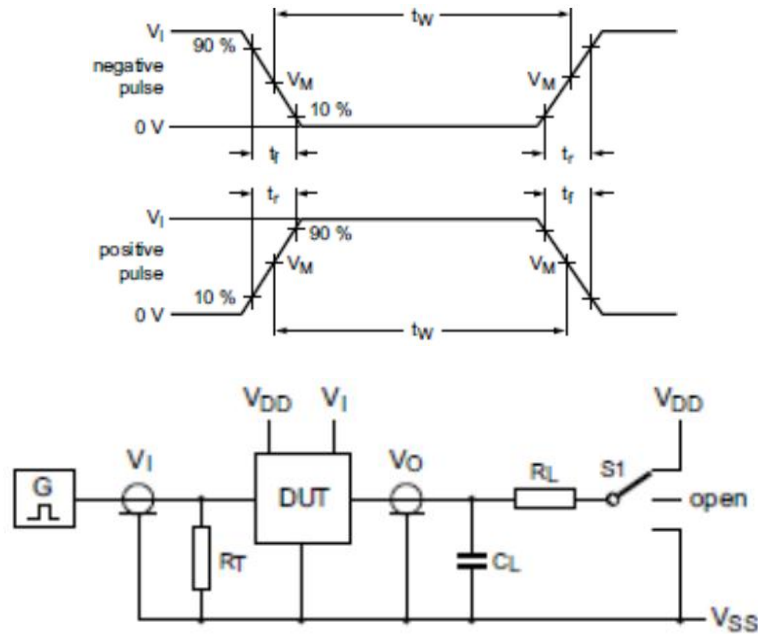


Figure 3. Test circuit for switching times

Definitions for test circuit:

DUT=Device Under Test.

$C_L$ =Load capacitance including jig and probe capacitance.

$R_T$ =Termination resistance should be equal to the output impedance  $Z_o$  of the pulse generator.

$R_L$ =Load resistance.

### AC Testing Waveforms

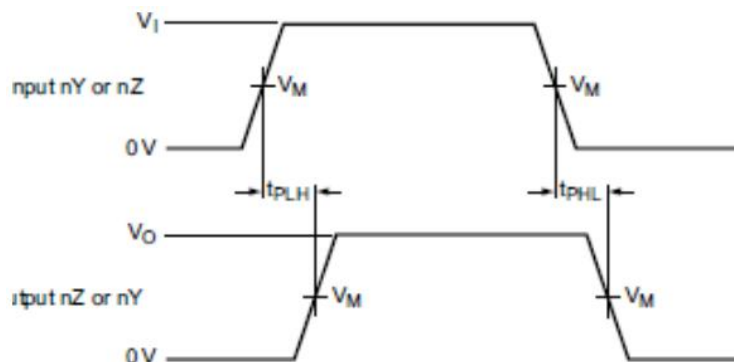


Figure 4. nY or nZ to nZ or nY propagation delays



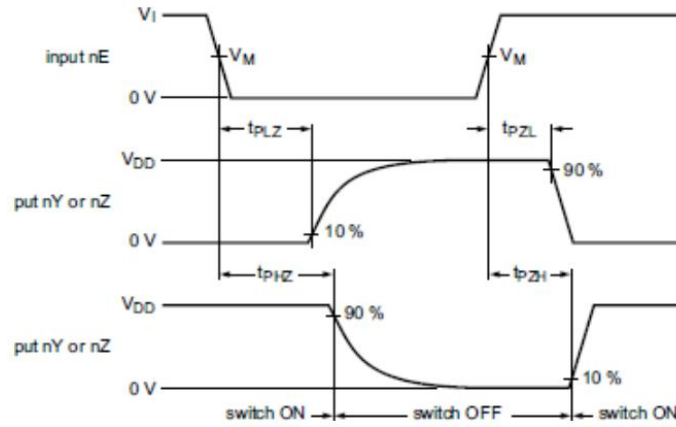


Figure 5. Enable and disable times

## AC Testing Circuit 2

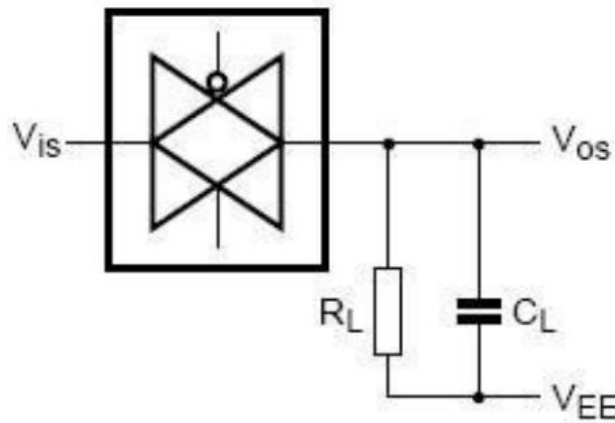


Figure 6. Square wave distortion degree of cut-off frequency and conduction frequency test pattern

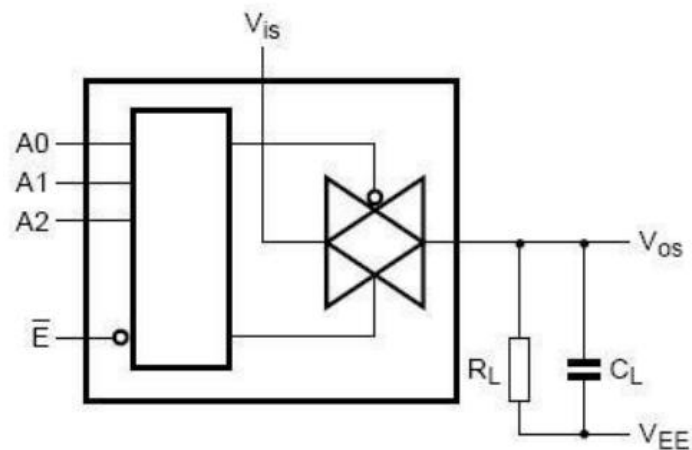


Figure 7. Crosstalk logical input/output test

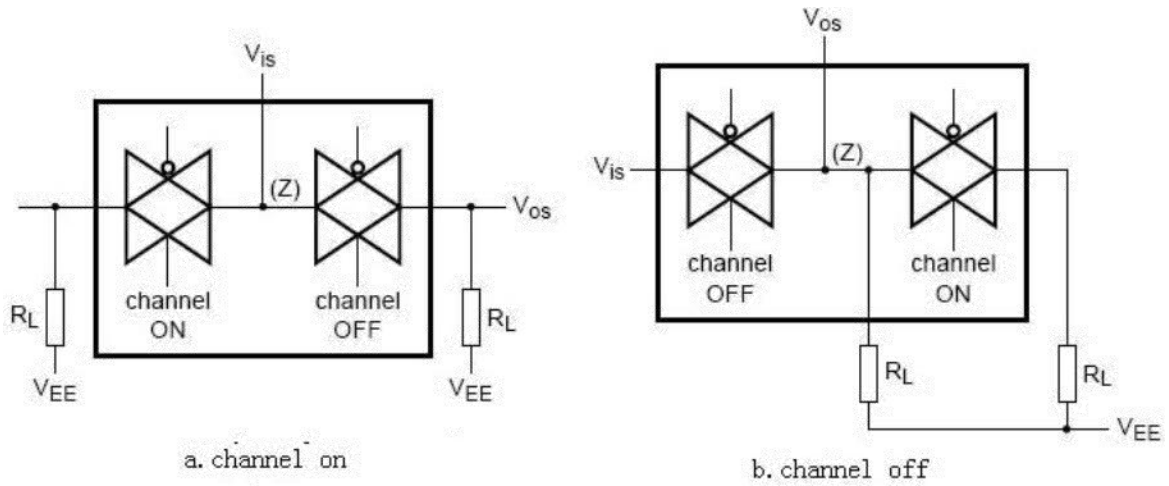
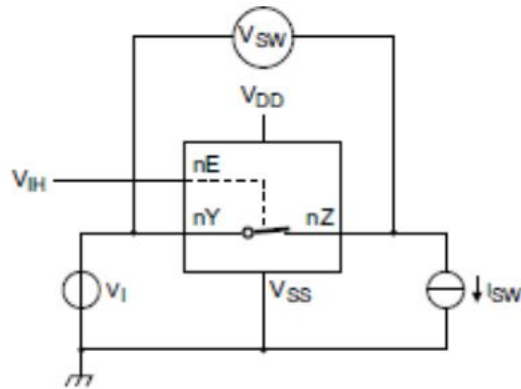


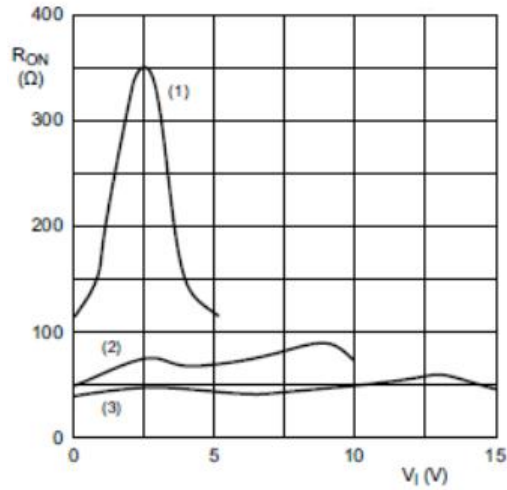
Figure 8. Inter channel Crosstalk

### On Resistance Waveform And Test Circuit



$$R_{ON} = V_{SW} / I_{SW}$$

Figure 9. Test circuit for measuring  $R_{ON}$



$I_{SW} = 200 \mu A.$   
 (1)  $V_{DD} = 5 V$   
 (2)  $V_{DD} = 10 V$   
 (3)  $V_{DD} = 15 V$

Figure 10. Typical  $R_{ON}$  as a function of input voltage

## Measurement Points

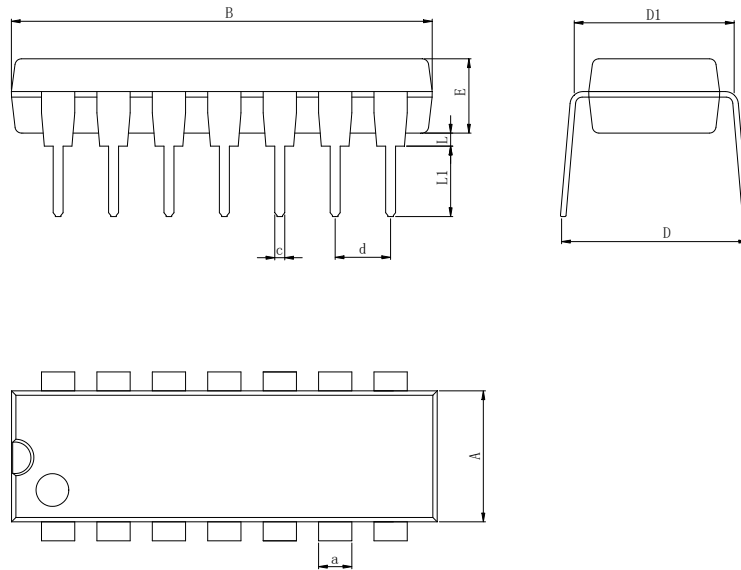
Supply voltage	Input	Output
$V_{DD}$	$V_M$	$V_M$
3V to 9V	$0.5 \times V_{DD}$	$0.5 \times V_{DD}$

## Test Data

Test	Input		Load		Switch
	$V_{is}$	$t_r, t_f$	$C_L$	$R_L$	
$t_{PHL}$	$V_{EE}$	20ns	50pF	10kΩ	$V_{DD}$
$t_{PLH}$	$V_{DD}$	20ns	50pF	10kΩ	$V_{EE}$
$t_{PZH}, t_{PHZ}$	$V_{DD}$	20ns	50pF	10kΩ	$V_{EE}$
$t_{PZL}, t_{PLZ}$	$V_{EE}$	20ns	50pF	10kΩ	$V_{DD}$
others	pulse	20ns	50pF	10kΩ	open

## Physical Dimensions

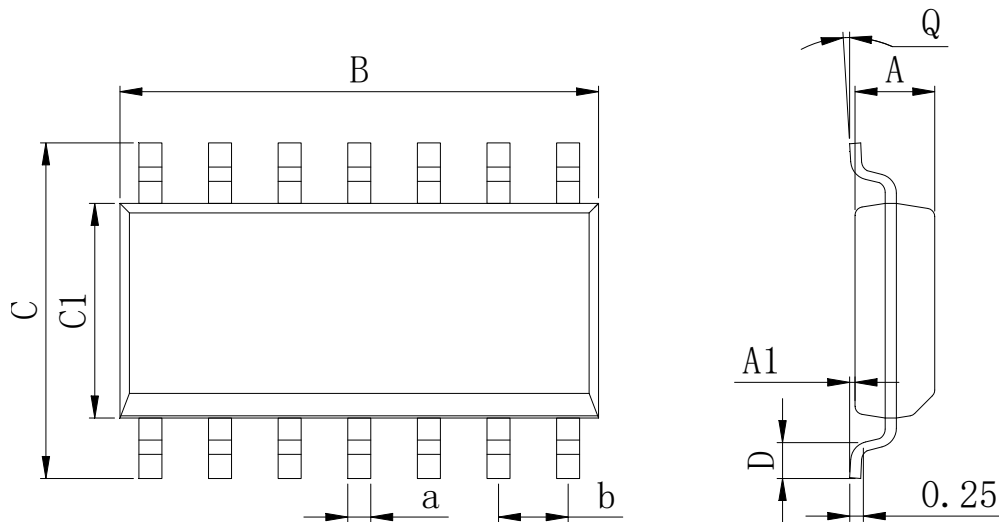
### DIP-14



Dimensions In Millimeters(DIP-14)

Symbol:	A	B	D	D1	E	L	L1	a	c	d
Min:	6.10	18.94	8.10	7.42	3.10	0.50	3.00	1.50	0.40	2.54 BSC
Max:	6.68	19.56	10.9	7.82	3.55	0.70	3.60	1.55	0.50	

### SOP-14

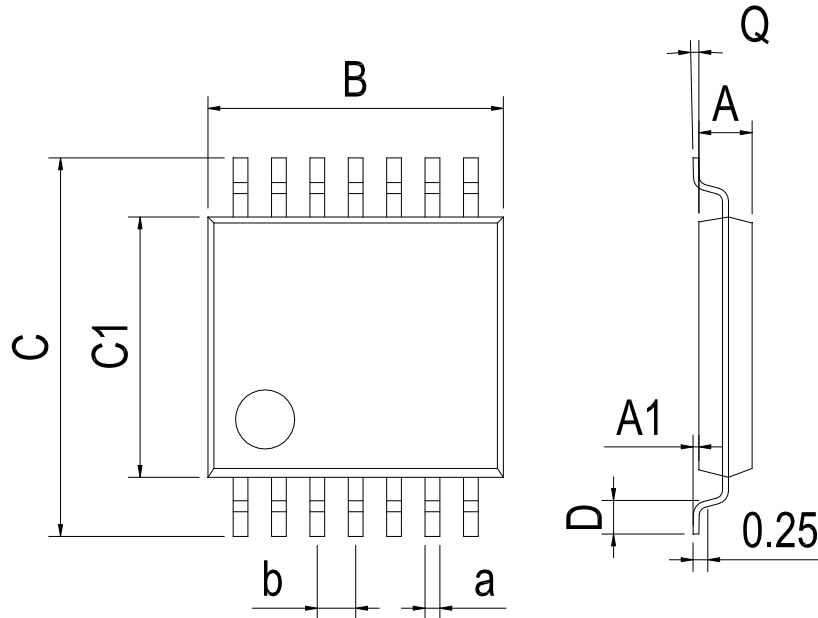


Dimensions In Millimeters(SOP-14)

Symbol:	A	A1	B	C	C1	D	Q	a	b
Min:	1.35	0.05	8.55	5.80	3.80	0.40	0°	0.35	1.27 BSC
Max:	1.55	0.20	8.75	6.20	4.00	0.80	8°	0.45	

**Physical Dimensions**

TSSOP-14



Dimensions In Millimeters(TSSOP-14)									
Symbol:	A	A1	B	C	C1	D	Q	a	b
Min:	0.85	0.05	4.90	6.20	4.30	0.40	0°	0.20	0.65 BSC
Max:	0.95	0.20	5.10	6.60	4.50	0.80	8°	0.25	

## Revision History

DATE	REVISION	PAGE
2015-5-28	New	1-15
2023-11-14	Document Reformatting、 Update DIP Package New Model	1-15、 1

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